# **BLF8G27LS-150V**; Power LDMOS transistor Rev. 4 — 1 September 2015

**AMPLEON** 

Product data sheet

### **Product profile**

#### 1.1 General description

150W LDMOS power transistor with improved video bandwidth for base station applications at frequencies from 2500 MHz to 2700 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case} = 25$  °C in a common source class-AB production test circuit.

Test signal	f	$I_{Dq}$	V <sub>DS</sub>	$P_{L(AV)}$	Gp	$\eta_{D}$	ACPR <sub>5M</sub>
	(MHz)	(mA)	(V)	(W)	(dB)	(%)	(dBc)
2-carrier W-CDMA	2600 to 2700	1300	28	45	18	30	-30 <sup>[1]</sup>

<sup>[1] 3</sup>GPP test model 1; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on CCDF; carrier spacing 5 MHz. Channel bandwidth is 3.84 MHz.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low R<sub>th</sub> providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth (60 MHz typical)
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent digital pre-distortion capability
- Internally matched for ease of use
- Integrated ESD protection
- Design optimized for gull-wing
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

#### 1.3 Applications

RF power amplifiers for W-CDMA base stations and multi carrier applications in the 2500 MHz to 2700 MHz frequency range

# 2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Graphic symbol
BLF8G27	7LS-150V (SOT1244B)		
1	drain	4 4 5	
2	gate	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	6.7→1 → 4,5
3	source [		6,7 - 4,5
4	decoupling lead	3	3
5	decoupling lead		aaa-003619
6	n.c.		
7	n.c.	6 2 7	
BLF8G27	7LS-150GV (SOT1244C)		
1	drain		,
2	gate	4 1 5 	6 7 → 1 → 4,5
3	source [	1	6,7 - 4,5
4	decoupling lead		3
5	decoupling lead		aaa-003619
6	n.c.	6 2   7 3	
7	n.c.		

<sup>[1]</sup> Connected to flange.

# 3. Ordering information

Table 3. Ordering information

Type number	Packa	Package		
	Name	Description	Version	
BLF8G27LS-150V	-	earless flanged ceramic package; 6 leads	SOT1244B	
BLF8G27LS-150GV	-	earless flanged ceramic package; 6 leads	SOT1244C	

# 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		<u>[1]</u> _	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability.

#### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
R <sub>th(j-c)</sub>	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_L$ = 45 W	0.30	K/W

#### 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 2.16 \text{ mA}$	65	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 216 mA	1.5	1.9	2.3	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 28 \text{ V}$	-	-	4.5	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$	-	40	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 11 V; $V_{DS}$ = 0 V	-	-	450	nA
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = 10 V; $I_{D}$ = 10.8 A	-	16	-	S
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 V;$ $I_D = 7.56 A$	-	0.06	-	Ω

#### Table 7. RF characteristics

Test signal: 2-carrier W-CDMA, 3GPP test model; 64 DPCH; PAR = 8.4 dB at 0.01 % probability on the CCDF, carrier spacing 5 MHz;  $f_1$  = 2602.5 MHz;  $f_2$  = 2607.5 MHz;  $f_3$  = 2692.5 MHz;  $f_4$  = 2697.5 MHz; RF performance at  $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $T_{case}$  = 25 °C; unless otherwise specified; in a class-AB production test circuit.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	$P_{L(AV)} = 45 \text{ W}$	16.8	18	-	dB
$RL_{in}$	input return loss	$P_{L(AV)} = 45 \text{ W}$	-	-10	-7	dB
$\eta_{D}$	drain efficiency	$P_{L(AV)} = 45 \text{ W}$	26	30	-	%
ACPR <sub>5M</sub>	adjacent channel power ratio (5 MHz)	$P_{L(AV)} = 45 \text{ W}$	-	-30	-26	dBc

#### 7. Test information

#### 7.1 Ruggedness in class-AB operation

The BLF8G27LS-150V and BLF8G27LS-150GV are capable of withstanding a load mismatch corresponding to VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS} = 28 \text{ V}$ ;  $I_{Dq} = 1300 \text{ mA}$ ;  $P_L = 150 \text{ W}$  (CW); f = 2600 MHz.

## 7.2 Impedance information

Table 8. **Typical impedance** 

Measured load-pull data;  $I_{Dq} = 1300 \text{ mA}$ ;  $V_{DS} = 28 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]
(MHz)	(Ω)	(Ω)
BLF8G27LS-150V		
2500	0.70 - j3.50	2.68 – j1.86
2600	1.10 – j4.40	2.86 – j2.03
2700	2.00 - j4.90	3.27 – j1.87
BLF8G27LS-150GV		
2500	1.00 – j5.70	2.35 – j4.04
2600	1.50 – j6.90	2.52 – j4.32
2700	2.10 – j8.00	3.21 – j4.36

[1]  $Z_S$  and  $Z_L$  defined in Figure 1.

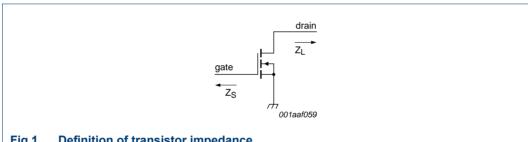


Fig 1. **Definition of transistor impedance** 

### 7.3 Test circuit

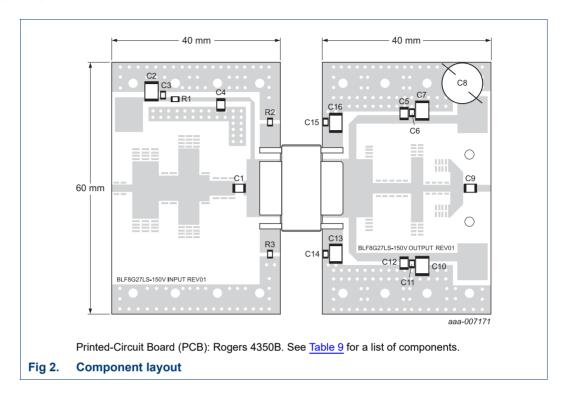


Table 9. List of components

See Figure 2 for component layout.

The used PCB material is Rogers RO4350B with a thickness of 0.76 mm.

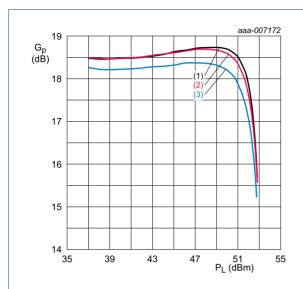
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	0.7 μF	11 ATC800B
C2	multilayer ceramic chip capacitor	1 μF	[2] Murata
C3	multilayer ceramic chip capacitor	100 nF	[2] Murata
C4, C5, C9, C12	multilayer ceramic chip capacitor	24 pF	11 ATC800B
C6, C11, C14, C15	multilayer ceramic chip capacitor	220 nF	[2] Murata
C7, C10, C13, C16	multilayer ceramic chip capacitor	4.7 μF, 50 V	[2] Murata
C8	electrolytic capacitor	> 470 μF, 63 V	
R1	chip resistor	4.7 $\Omega$ , 1 % tolerance	SMD 1206
R2, R3	chip resistor	0 Ω	SMD 1206

<sup>[1]</sup> American Technical Ceramics type 800B or capacitor of same quality.

<sup>[2]</sup> Murata or capacitor of same quality.

#### 7.4 Graphical data

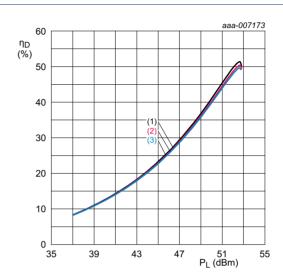
#### 7.4.1 Pulsed CW



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $t_p$  = 100  $\mu s;$   $\delta$  = 10 %.

- (1) f = 2600 MHz
- (2) f = 2655 MHz
- (3) f = 2700 MHz

Fig 3. Power gain as a function of output power; typical values

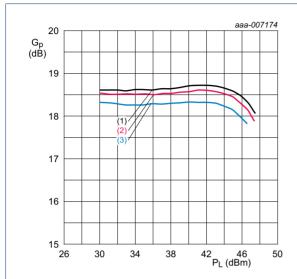


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %.

- (1) f = 2600 MHz
- (2) f = 2655 MHz
- (3) f = 2700 MHz

Fig 4. Drain efficiency as a function of out power; typical values

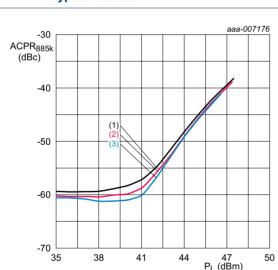
#### 7.4.2 IS-95



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

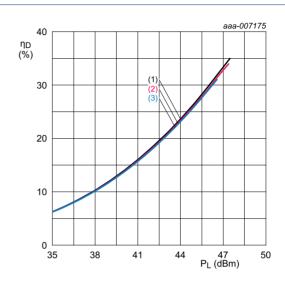
Fig 5. Power gain as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

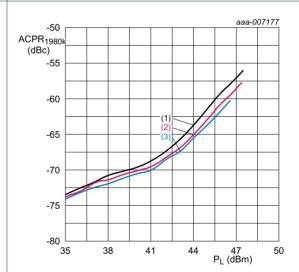
Fig 7. Adjacent channel power ratio (885 kHz) as a function of output power; typical values



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 6. Drain efficiency as a function of output power; typical values

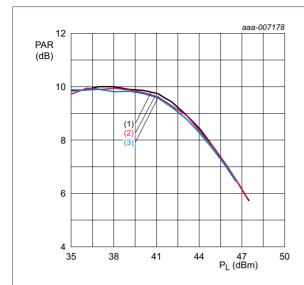


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 8. Adjacent channel power ratio (1980 kHz) as a function of output power; typical values

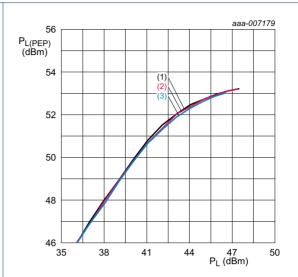
**Power LDMOS transistor** 



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 9. Peak-to-average power ratio as a function of output power; typical values

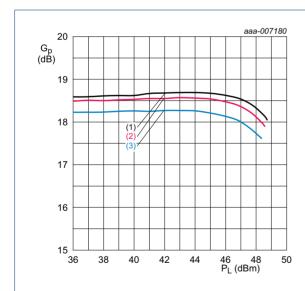


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 10. Peak envelope power load power as a function of output power; typical values

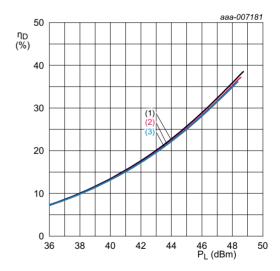
#### 7.4.3 1-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

Fig 11. Power gain as a function of output power; typical values

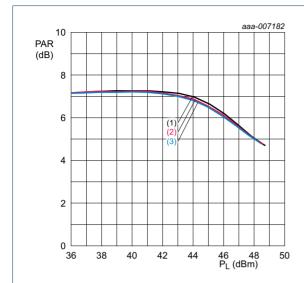


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

Fig 12. Drain efficiency as a function of output power; typical values

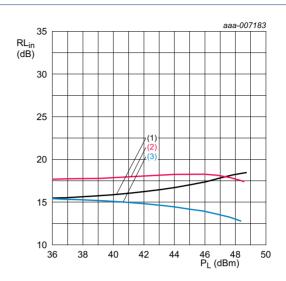
**Power LDMOS transistor** 



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

Fig 13. Peak-to-average power ratio as a function of output power; typical values

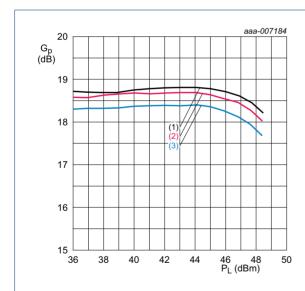


 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2602.5 MHz
- (2) f = 2655 MHz
- (3) f = 2697.5 MHz

Fig 14. Input return loss as a function of output power; typical values

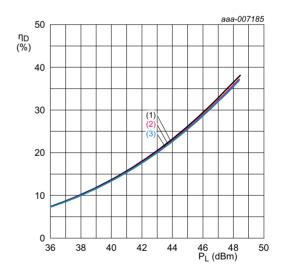
#### 7.4.4 2-Carrier W-CDMA



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 15. Power gain as a function of output power; typical values

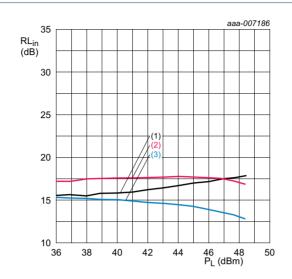


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 16. Drain efficiency as a function of output power; typical values

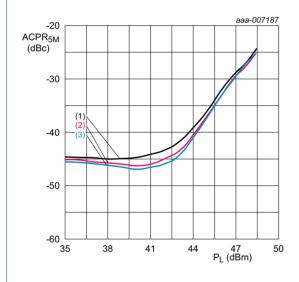
**Power LDMOS transistor** 



 $V_{DS} = 28 \text{ V}; I_{Dq} = 1300 \text{ mA}.$ 

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

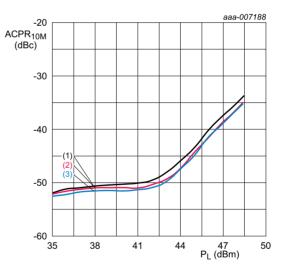
Fig 17. Input return loss as a function of output power; typical values



 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 18. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

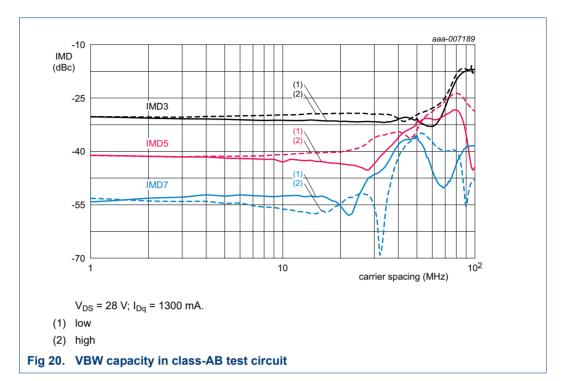


 $V_{DS}$  = 28 V;  $I_{Dq}$  = 1300 mA.

- (1) f = 2605 MHz
- (2) f = 2655 MHz
- (3) f = 2695 MHz

Fig 19. Adjacent channel power ratio (10 MHz) as a function of output power; typical values

#### 7.4.5 2-Tone VBW



## 8. Package outline

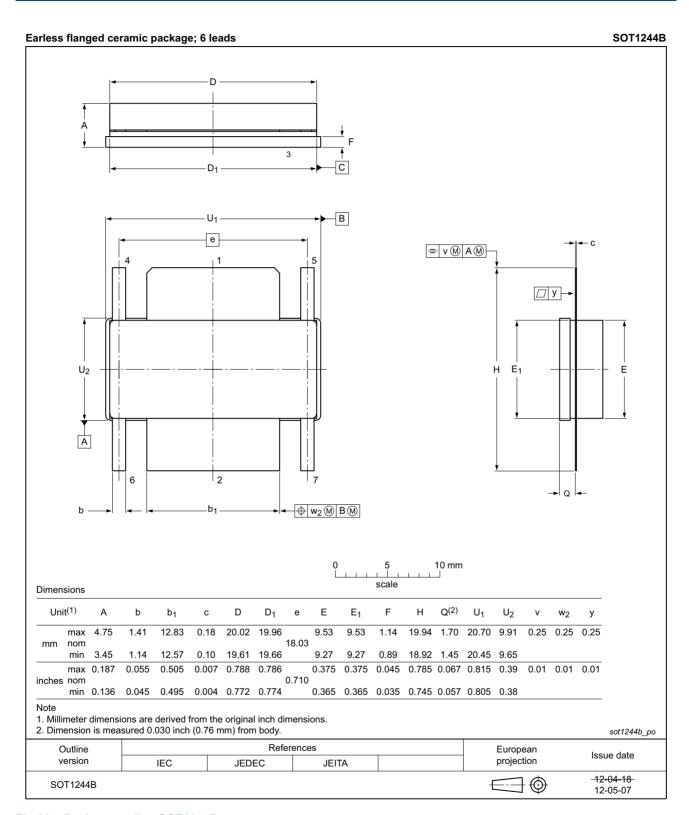


Fig 21. Package outline SOT1244B

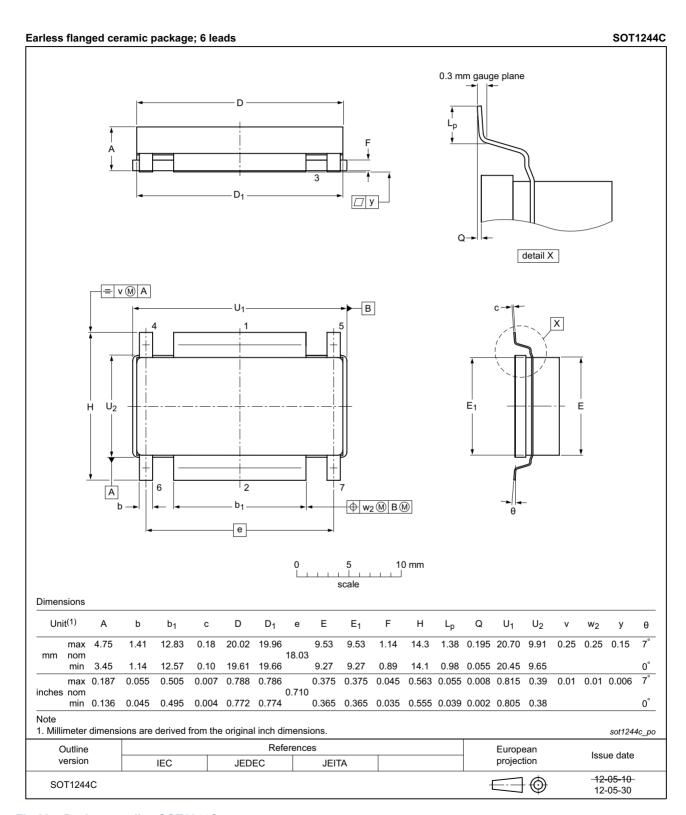


Fig 22. Package outline SOT1244C

# 9. Handling information

#### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

### 10. Abbreviations

Table 10. Abbreviations

Acronym	Description	
3GPP	3rd Generation Partnership Project	
CCDF	Complementary Cumulative Distribution Function	
CW	Continuous Wave	
DPCH	Dedicated Physical CHannel	
ESD	ElectroStatic Discharge	
IS-95	Interim Standard 95	
LDMOS	Laterally Diffused Metal Oxide Semiconductor	
PAR	Peak-to-Average Ratio	
SMD	Surface Mounted Device	
VBW	Video BandWidth	
VSWR	Voltage Standing Wave Ratio	
W-CDMA	Wideband Code Division Multiple Access	

# 11. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF8G27LS-150V_8G27LS-150GV#4	20150901	Product data sheet		BLF8G27LS-150V_ 8G27LS-150GV v.3	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
BLF8G27LS-150V_8G27LS-150GV v.3	20130626	Product data sheet	-	BLF8G27LS-150V_ 8G27LS-150GV v.2	
BLF8G27LS-150V_8G27LS-150GV v.2	20130422	Objective data sheet	-	BLF8G27LS-150V_ 8G27LS-150GV v.1	
BLF8G27LS-150V_8G27LS-150GV v.1	20130129	Objective data sheet	-	-	

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition		
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.		
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.		
Product [short] data sheet	Production	This document contains the product specification.		

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <a href="https://www.ampleon.com">https://www.ampleon.com</a>.

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BLF8G27LS-150V 8G27LS-150GV#4

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**Power LDMOS transistor** 

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For sales office addresses, please visit: http://www.ampleon.com/sales

# **AMPLEON**

# BLF8G27LS-150(G)V

**Power LDMOS transistor** 

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